

PATENT

AMENDMENTS TO THE SPECIFICATION

Please amend the title in all instances as follows:

~~MOS TRANSISTOR AND METHOD OF FORMING A MOS TRANSISTOR WITH A LAYER OF SILICON GERMANIUM CARBON~~

Please insert the following paragraph before the first paragraph on page 1:

This is a divisional application of Application Serial No. 10/315,394 filed on December 10, 2002.

On page 1, please insert as the first paragraph:

RELATED APPLICATION

The present invention is related to Application Serial No. 10/315,300 for "MOS Transistor and Method of Forming the Transistor with a Channel Region in a Layer of Composite Material" by Abdalla Aly Naem filed on an even date herewith.

BRIEF DESCRIPTION OF THE DRAWINGS